

# Freeform Search

<b>Database:</b>	<input checked="" type="checkbox"/> US Pre-Grant Publication Full-Text Database <input type="checkbox"/> US Patents Full-Text Database <input type="checkbox"/> US OCR Full-Text Database <input type="checkbox"/> EPO Abstracts Database <input type="checkbox"/> JPO Abstracts Database <input type="checkbox"/> Derwent World Patents Index <input type="checkbox"/> IBM Technical Disclosure Bulletins
<b>Term:</b>	L16 and ("single crystal extrinsic" near5 (base near3 transistor))
<b>Display:</b>	<input type="text" value="10"/> Documents in <u>Display Format:</u> <input type="text" value="T1"/> Starting with Number <input type="text" value="1"/>
<b>Generate:</b>	<input type="radio"/> Hit List <input checked="" type="radio"/> Hit Count <input type="radio"/> Side by Side <input type="radio"/> Image

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**Search History**
**DATE:** Thursday, August 12, 2004    [Printable Copy](#)    [Create Case](#)
**Set Name** **Query**

side by side

**Hit Count** **Set Name**  
 result set

*DB=USPT; PLUR=YES; OP=OR*

<u>L21</u>	L16 and ("single crystal extrinsic" near5 (base near3 transistor))	0	<u>L21</u>
<u>L20</u>	L16 and ("single crystal extrinsic" near5 (base near3 transistor))	0	<u>L20</u>
<u>L19</u>	L16 and ("single crystal intrinsic" near5 (base near3 transistor))	0	<u>L19</u>
<u>L18</u>	L16 and ("single crystal" near5 (base near3 transistor))	10	<u>L18</u>
<u>L17</u>	L16 and ("single crystal" near5 base)	46	<u>L17</u>
<u>L16</u>	L15 and soi	1468	<u>L16</u>
<u>L15</u>	"bipolar transistor"	28084	<u>L15</u>
<u>L14</u>	bipolar	59573	<u>L14</u>

*DB=TDBD; PLUR=YES; OP=OR*

<u>L13</u>	L12	0	<u>L13</u>
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*DB=DWPI; PLUR=YES; OP=OR*

<u>L12</u>	L11	0	<u>L12</u>
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*DB=JPAB; PLUR=YES; OP=OR*

<u>L11</u>	L10	0	<u>L11</u>
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*DB=EPAB; PLUR=YES; OP=OR*

<u>L10</u>	L9	0	<u>L10</u>
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*DB=USOC; PLUR=YES; OP=OR*

L9 L8

0 L9

*DB=PGPB; PLUR=YES; OP=OR*

L8 L7

0 L8

*DB=USPT; PLUR=YES; OP=OR*

L7 L6 and HDP

0 L7

L6 L4 and soi

5 L6

L5 L4 and traverse and longitudinal

1 L5

L4 transistor\$ same (isolation near5 TEOS)

33 L4

L3 NFET same (isolation near5 TEOS)

0 L3

L2 L1 and "first isolation" and "second isolation"

4 L2

L1 isolation same TEOS same HDP

76 L1

END OF SEARCH HISTORY